FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
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LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

Date Submitted to PTO: JUNE 9, 2004

ATTY DOCKET NO. 3230-86	APPLICATION NO. 10/781,892
APPLICANT WU et al.	
FILING DATE February 20, 2004	GROUP ~~2811~~ 2891

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JUN. 0 9 2004							

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

AICS		Y. Honda et al.; "Selective Area Growth Of GaN Microstructure On Patterned (111) and (001) Si Substrates"; *Journal of Crystal Growth 230";* pp. 346-350; 2001
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		Jaime A. Freitas, et al.; "Optical And Structural Properties Of Lateral Epitaxial Overgrown GaN Layers"; *Journal of Crystal Growth 189/190*; pp. 92-96; 1998
		Shuji Nakamura et al.; "Present Status Of InGaN/GaN/AlGaN-based Laser Diodes"; *Journal of Crystal Growth 189/190*; pp. 820-825; 1998
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		Tsvetanka S. Zheleva, et al.; "Lateral Epitaxy and Dislocation Density Reduction in Selectively Grown GaN Structures"; *Journal of Crystal Growth 222*; pp. 706-718; 2001
		W. S. Wong et al.; "In $XGa_{1-x}N$ Light Emitting Diodes on Si Substrates Fabricated by Pd-In Metal Bonding and Laser Lift-off"; *Applied Physics Letters Volume 77; Number 18*;pp. 2822-2824; 2000
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EXAMINER	Asoke Kumar Sarkar	DATE CONSIDERED	6/8/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.